

Apple. No. 10/023,825
Reply to Office action of 09/17/2003

Amendments to the ABSTRACT:

Cancel the ABSTRACT and replace it with the following:

ABSTRACT

A polysilicon layer of a gate structure is covered by an implant blocking layer (e.g., silicon nitride). The implant blocking layer blocks introduction of implanted dopants while implanting an initial dose of first conductivity type dopant (e.g., for drain extension regions). The implant blocking layer is then removed and an additional dose of first conductivity type dopant is implanted to form the main source/drain regions. Then, metal is deposited and reacted to form a conductive silicide.